

Notice of Allowability	Application No.	Applicant(s)
	10/817,468	PIAZZA ET AL.
	Examiner David Nhu	Art Unit 2818

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address--

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1. This communication is responsive to 1/14/05.
2. The allowed claim(s) is/are 1-9 and 14-19.
3. The drawings filed on 02 April 2004 are accepted by the Examiner.
4. Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 - a) All
 - b) Some*
 - c) None
 of the:
 1. Certified copies of the priority documents have been received.
 2. Certified copies of the priority documents have been received in Application No. 10/255,392.
 3. Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

* Certified copies not received: _____

Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.
THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.

5. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.
6. CORRECTED DRAWINGS (as "replacement sheets") must be submitted.
 - (a) including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached
 - 1) hereto or 2) to Paper No./Mail Date _____.
 - (b) including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date _____.
7. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

Attachment(s)

1. Notice of References Cited (PTO-892)
2. Notice of Draftsperson's Patent Drawing Review (PTO-948)
3. Information Disclosure Statements (PTO-1449 or PTO/SB/08),
Paper No./Mail Date _____
4. Examiner's Comment Regarding Requirement for Deposit
of Biological Material
5. Notice of Informal Patent Application (PTO-152)
6. Interview Summary (PTO-413),
Paper No./Mail Date _____
7. Examiner's Amendment/Comment
8. Examiner's Statement of Reasons for Allowance
9. Other _____.



EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the change and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

Claims 10-13 are canceled.

Claim 1 (currently amended), line 12, "the second trench" should be –the second parallel trench– , line 20, "each first trench, each second trench" should be –each first parallel trench, each second parallel trench–

REASONS FOR ALLOWANCE

2. Claims 1-9, 14-19 are allowed.

3. The following is an examiner's statement of reasons for allowance: None of the references of record teaches or suggests as cited in claims 1, 14: A method for forming in monolithic form a DRAM type memory, including the steps of: forming, on a single-crystal semiconductor substrate, parallel strips including a lower insulating layer, a strongly-conductive layer, a single-crystal semiconductor layer, and an upper insulating layer; forming, perpendicular to the parallel strips, in the upper insulating layer and in at least a portion of the single-crystal semiconductor layer, first and second parallel trenches, each of the first and second parallel trenches being shared by neighboring cells; forming, in each of the first parallel trenches, a first conductive line according to a strip width; forming, in each of the second parallel trenches, a pair of second distinct parallel conductive line, insulated from layers peripheral to the second parallel trenches;

filling the first and second parallel trenches with an insulating material; removing the remaining portions of the upper insulating layer; and depositing a conductive layer, wherein the first and second parallel trenches are formed in the upper insulating layer and at least a portion of the single-crystal semiconductor layer so that the first parallel trenches have a minimum width, and the second parallel trenches have a width which is twice that of the first parallel trenches, two neighboring parallel trenches being separated by a minimum interval, each first trench being surround with two second parallel trenches and each second trench being surrounded with two first parallel trenches.

4. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

5. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure: Piazza et al(6,740,919 B2): RAM.
6. Any inquiry concerning this communication on earlier communications from the examiner should be directed to David Nhu, (571)272-1792. The examiner can normally be reached on Monday-Friday from 7:30 AM to 5:00 PM.

The examiner's supervisor, David Nelms can be reached on (571)272-1787.

The fax phone number for the organization where this application or proceeding is assigned is (703)872-9306.

Art Unit: 2818

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956

David Nhu

pn



Art Unit: 2818

DAVID NHU
PRIMARY EXAMINER